

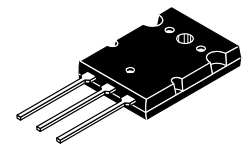
Designer's™ Data Sheet
**Complementary NPN-PNP
Silicon Power Bipolar Transistor**

- The MJL3281A and MJL1302A are PowerBase power transistors for high power audio, disk head positioners and other linear applications.
- Designed for 100 W Audio Frequency
- Gain Complementary:
 - Gain Linearity from 100 mA to 7 A
 - High Gain — 60 to 175
 - $h_{FE} = 45$ (Min) @ $I_C = 8$ A
- Low Harmonic Distortion
- High Safe Operation Area — 1 A/100 V @ 1 sec
- High f_T — 30 MHz Typical

**NPN
MJL3281A*
PNP
MJL1302A***

*Motorola Preferred Device

**15 AMPERE
COMPLEMENTARY
SILICON POWER
TRANSISTORS
200 VOLTS
200 WATTS**



**CASE 340G-02, STYLE 2
TO-264**

MAXIMUM RATINGS ($T_J = 25^\circ\text{C}$ unless otherwise noted)

Rating	Symbol	Value	Unit
Collector-Emitter Voltage	V_{CEO}	200	Vdc
Collector-Base Voltage	V_{CBO}	200	Vdc
Emitter-Base Voltage	V_{EBO}	7	Vdc
Collector-Emitter Voltage — 1.5 V	V_{CEX}	200	Vdc
Collector Current — Continuous — Peak (1)	I_C	15 25	Adc
Base Current — Continuous	I_B	1.5	Adc
Total Power Dissipation @ $T_C = 25^\circ\text{C}$ Derate Above 25°C	P_D	200 1.43	Watts W/ $^\circ\text{C}$
Operating and Storage Junction Temperature Range	T_J, T_{stg}	-65 to +150	$^\circ\text{C}$

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Case	$R_{\theta JC}$	0.7	$^\circ\text{C/W}$

(1) Pulse Test: Pulse Width = 5 ms, Duty Cycle <10%.

Designer's Data for "Worst Case" Conditions — The Designer's Data Sheet permits the design of most circuits entirely from the information presented. SOA Limit curves — representing boundaries on device characteristics — are given to facilitate "worst case" design.

Designer's is a trademark of Motorola, Inc.

Preferred devices are Motorola recommended choices for future use and best overall value.

MJL3281A**ELECTRICAL CHARACTERISTICS** ($T_C = 25^\circ\text{C}$ unless otherwise noted)

Characteristic	Symbol	Min	Typ	Max	Unit
OFF CHARACTERISTICS					
Collector–Emitter Sustaining Voltage ($I_C = 100\text{ mAdc}$, $I_B = 0$)	$V_{CEO(sus)}$	200	—	—	Vdc
Emitter–Base Voltage ($I_E = 100\text{ }\mu\text{Adc}$, $I_C = 0$)	V_{EBO}	7	—	—	Vdc
Collector Cutoff Current ($V_{CB} = 200\text{ Vdc}$, $I_E = 0$)	I_{CBO}	—	—	50	μAdc
Emitter Cutoff Current ($V_{EB} = 5\text{ Vdc}$, $I_C = 0$)	I_{EBO}	—	—	5	μAdc
Emitter Cutoff Current ($V_{EB} = 7\text{ Vdc}$, $I_C = 0$)	I_{EBO}	—	—	25	μAdc

SECOND BREAKDOWN

Second Breakdown Collector with Base Forward Biased ($V_{CE} = 50\text{ Vdc}$, $t = 1\text{ s}$ (non–repetitive)) ($V_{CE} = 100\text{ Vdc}$, $t = 1\text{ s}$ (non–repetitive))	$I_{S/b}$	4 1	— —	— —	Adc
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ON CHARACTERISTICS

DC Current Gain ($I_C = 100\text{ mAdc}$, $V_{CE} = 5\text{ Vdc}$) ($I_C = 1\text{ Adc}$, $V_{CE} = 5\text{ Vdc}$) ($I_C = 3\text{ Adc}$, $V_{CE} = 5\text{ Vdc}$) ($I_C = 5\text{ Adc}$, $V_{CE} = 5\text{ Vdc}$) ($I_C = 7\text{ Adc}$, $V_{CE} = 5\text{ Vdc}$) ($I_C = 8\text{ Adc}$, $V_{CE} = 5\text{ Vdc}$) ($I_C = 15\text{ Adc}$, $V_{CE} = 5\text{ Vdc}$)	h_{FE}	60 60 60 60 60 45 12	125 — — — 115 — 35	175 175 175 175 175 — —	
Collector–Emitter Saturation Voltage ($I_C = 10\text{ Adc}$, $I_B = 1\text{ Adc}$)	$V_{CE(sat)}$	—	—	3	Vdc

DYNAMIC CHARACTERISTICS

Current–Gain — Bandwidth Product ($I_C = 1\text{ Adc}$, $V_{CE} = 5\text{ Vdc}$, $f_{test} = 1\text{ MHz}$)	f_T	—	30	—	MHz
Output Capacitance ($V_{CB} = 10\text{ Vdc}$, $I_E = 0$, $f_{test} = 1\text{ MHz}$)	C_{ob}	—	—	600	pF

(1) Pulse Test: Pulse Width = 300 μs , Duty Cycle $\leq 2\%$.

TYPICAL CHARACTERISTICS

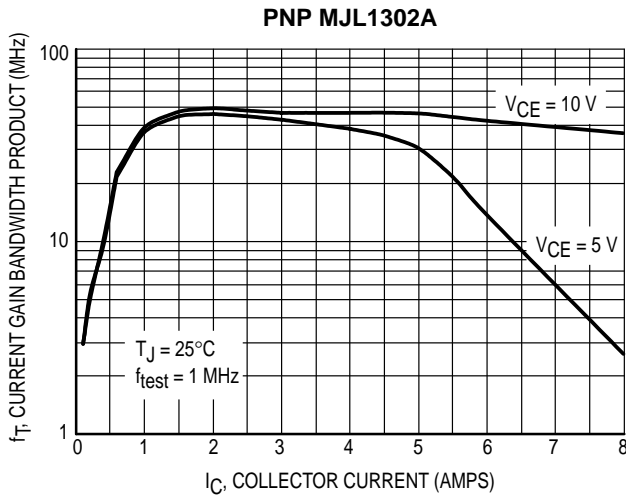


Figure 1. Current-Gain — Bandwidth Product

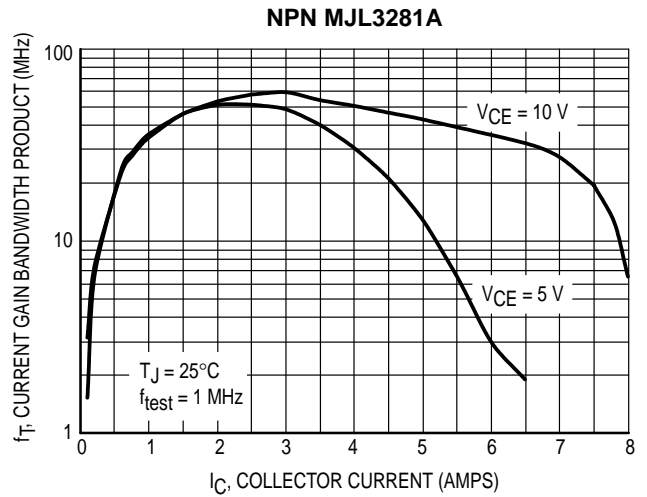


Figure 2. Current-Gain — Bandwidth Product

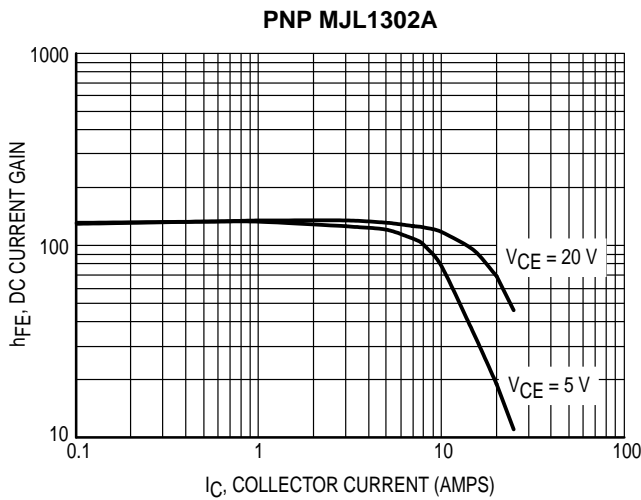


Figure 3. DC Current Gain

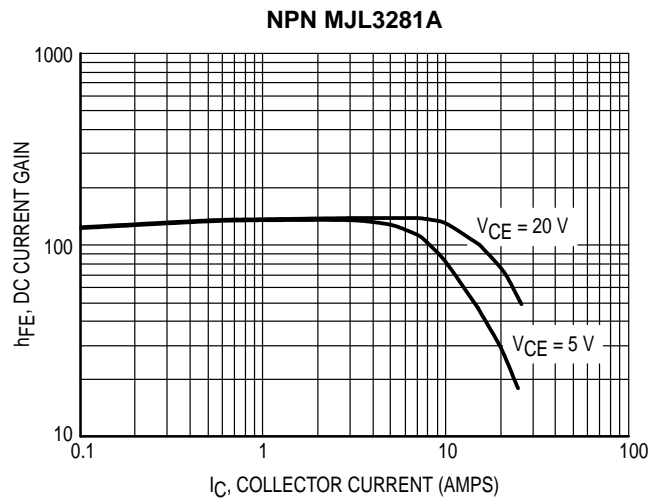


Figure 4. DC Current Gain

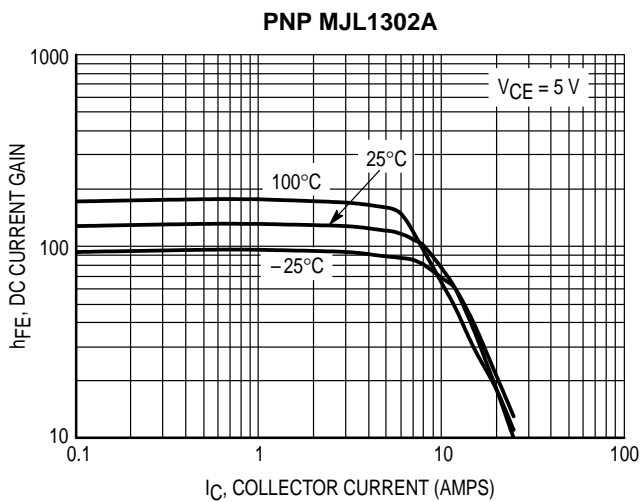


Figure 5. DC Current Gain, $V_{CE} = 5 V$

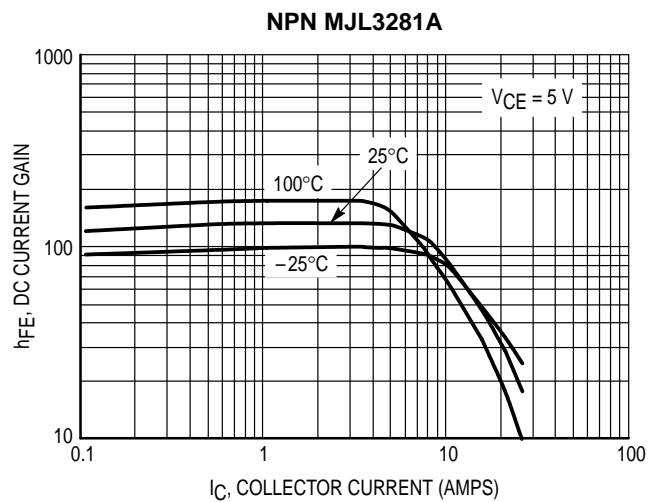


Figure 6. DC Current Gain, $V_{CE} = 5 V$

TYPICAL CHARACTERISTICS

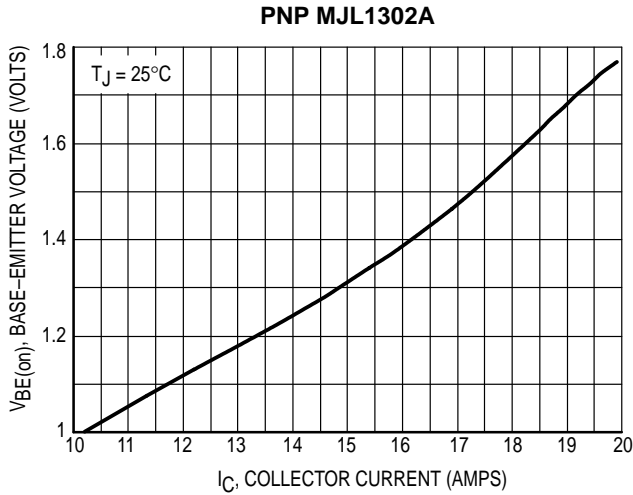


Figure 7. Typical Base-Emitter Voltage

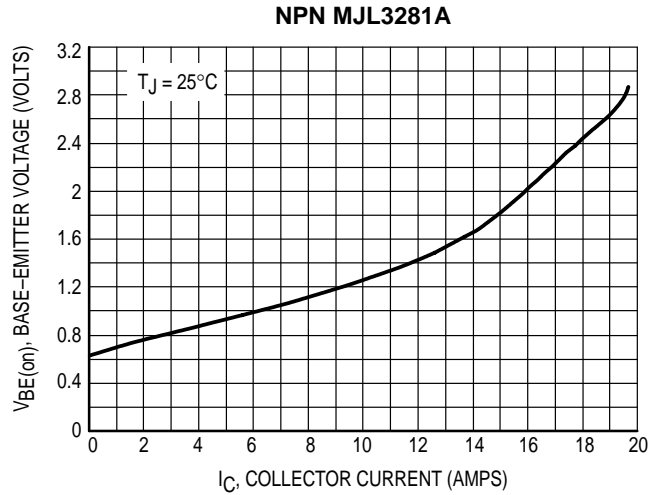


Figure 8. Typical Base-Emitter Voltage

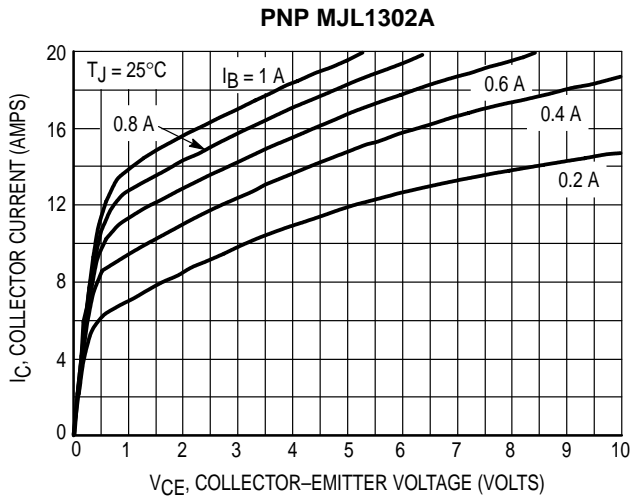


Figure 9. Typical Output Characteristics

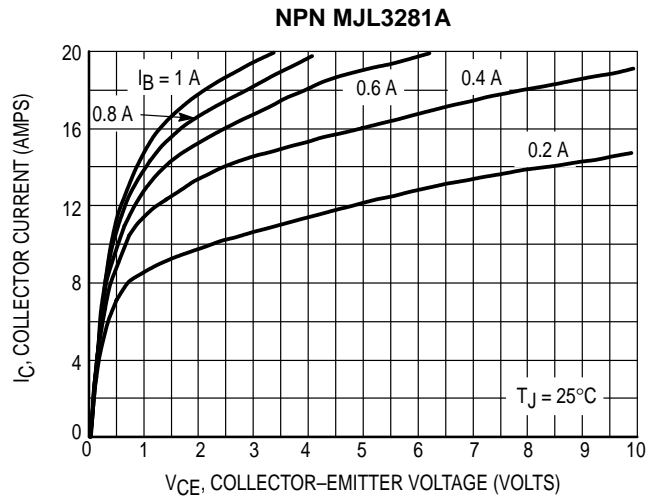


Figure 10. Typical Output Characteristics

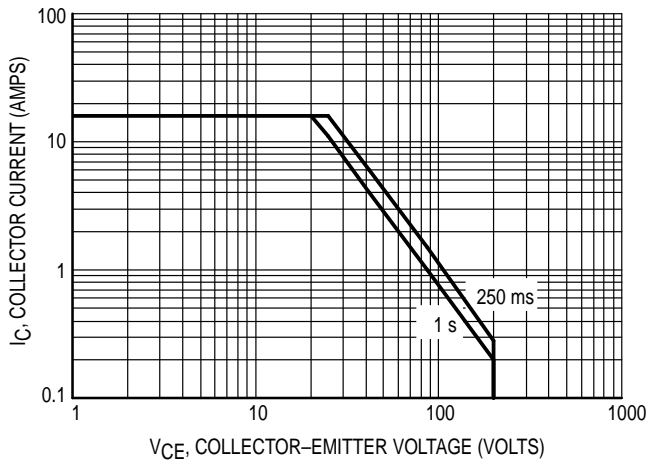
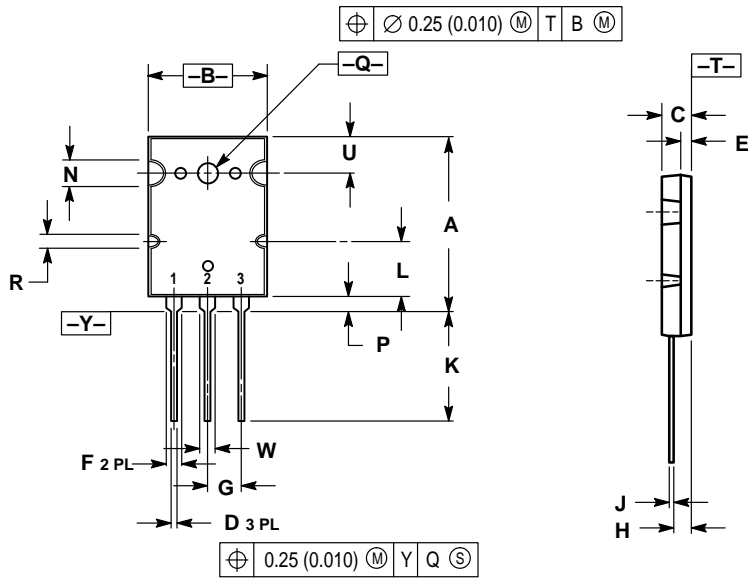


Figure 11. Forward Bias Safe Operating Area (FBSOA)

There are two limitations on the power handling ability of a transistor; average junction temperature and secondary breakdown. Safe operating area curves indicate $I_C - V_{CE}$ limits of the transistor that must be observed for reliable operation; i.e., the transistor must not be subjected to greater dissipation than the curves indicate.

The data of Figure 11 is based on $T_{J(pk)} = 200^\circ\text{C}$; T_C is variable depending on conditions. At high case temperatures, thermal limitations will reduce the power than can be handled to values less than the limitations imposed by second breakdown.

PACKAGE DIMENSIONS



NOTES:
 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
 2. CONTROLLING DIMENSION: MILLIMETER.

DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	2.8	2.9	1.102	1.142
B	19.3	20.3	0.760	0.800
C	4.7	5.3	0.185	0.209
D	0.93	1.48	0.037	0.058
E	1.9	2.1	0.075	0.083
F	2.2	2.4	0.087	0.102
G	5.45 BSC		0.215 BSC	
H	2.6	3.0	0.102	0.118
J	0.43	0.78	0.017	0.031
K	17.6	18.8	0.693	0.740
L	11.0	11.4	0.433	0.449
N	3.95	4.75	0.156	0.187
P	2.2	2.6	0.087	0.102
Q	3.1	3.5	0.122	0.137
R	2.15	2.35	0.085	0.093
U	6.1	6.5	0.240	0.256
W	2.8	3.2	0.110	0.125

STYLE 2:
 PIN 1. BASE
 2. COLLECTOR
 3. EMITTER

CASE 340G-02
 TO-264
 ISSUE E

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